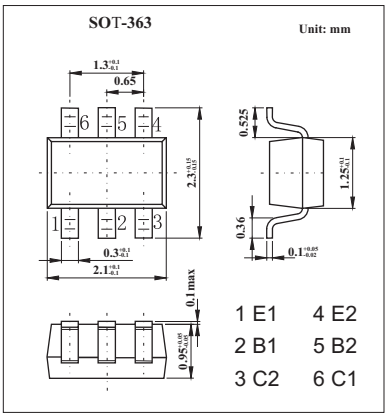
TY Semicondutor®

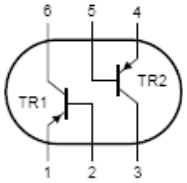
Product specification

KC856S(BC856S)



■ Features

- ●Two transistors in one package
- ●Reduces number of components and board space
- ●No mutual interference between the transistors.



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-65	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-100	mA
Power Dissipation	P_D	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	416	℃/W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Cutoff Current	I_{CBO}	V_{CB} =- 30 V, I_E = 0			-15	nA
		V_{CB} =- 30 V, I_E = 0, T_A = 150℃			-5.0	μ A
Emitter- cutoff current	I_{EBO}	I_C=0,V_{EB}=-5V			-100	nA
DC Current Gain	h_{FE}	I_C = -2.0 mA, V_{CE} = -5.0 V	110			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -10 mA, I_B =- 0.5 mA			-100	mV
		I_C = -100 mA, I_B =- 5.0 mA			-300	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = -10 mA, I_B=-0.5mA		700		m V
Output Capacitance	C_{ob}	V_{CB} = -10 V, f = 1.0 MHz			2.5	pF
Transistion frequency	f_T	I_C = -10 mA, V_{CE} = -5.0V,f = 100 mHz	100			MHz

■ Marking

Marking	5F